Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph spanning pages 9 and 10 with the following rewritten paragraph:

The horizontal part 11b is communicated with the main shield body 11a via a curvature 11b (first curvature). The rising part 11c is communicated with the horizontal part 11b via a curvature 11bc (second curvature). Further, the mounting part 11d is communicated with the main shield body 11a via a curvature 11ad (third curvature). Here, each of an inside corner $11bc_1$ of the curvature 11bc and an inside corner $11ad_1$ of the curvature 11ad is formed of a curved surface having for example a circular arc-cross section. Each ~~diameter~~ distance (R_2, R_3) from the center (O_2, O_3), namely each radius of ~~curvatures~~ curvature, is 5mm or more (see Fig. 6). Further, the curvature 11ab is formed of a curved surface having an elliptic arc-cross section. An inside corner $11ab_1$ is also formed of a curved face having an elliptic arc-cross section. A ~~diameter~~ radius (R_1) from the center (O_1) is 100mm or more, 150mm for example (see Fig. 6). If each distance or radius (R_1, R_2) from the center (O_2, O_3) is set to 5mm or more, stress does not occur and cracks do not appear due to a difference of a heat expansion coefficient between graphite and silicon carbide. If each distance or radius (R_2, R_3) is smaller than 5mm, stress occurs by the difference of the heat expansion coefficient of graphite and silicon carbide and cracks appear. In addition, if necessary, a curved surface with R 5mm or more can be formed at an outside corner of each curvature and the end of the base material.

Please replace paragraph starting at page 13, line 1, with the following rewritten paragraph:

Thus, by appropriately combining the ring members $11Af_1$, $11Af_2$, and $11Af_3$, the temperature range 1050~1150°C in which COP (Crystal Originated Particle) density is influenced can be easily adjusted. The ratio of single crystallization can be improved. Further, even if particles or fragments originate from the heat insulating material 11Ae, the rising part 11Ac and the cover 11Af prevent them from dropping on the melt.

Please replace Table 1, on page 14, with the following Table:

	inside corner (mm)	Stress of silicon carbide film (kgf/mm^2)	Stress of graphite base material (kgf/mm^2)
example	5	~~13~~ 10	~~1.2~~ 1.0
conventional apparatus	1	~~10~~ 13	~~1.0~~ 1.2

Please replace paragraph starting at page 14, line 5 (below Table 1), with the following rewritten paragraph:

As can be understood from Table 1, it was confirmed that heat stress generated at the graphite base material and the silicon carbide film can be dispersed in the ratio of ~~about 20-30%~~ about 20%.